



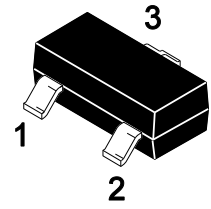
# BAV99<sup>†</sup>

## Silicon Epitaxial Planar Switching Diode

### Features

- For surface mount applications
- Fast reverse recovery time
- Ideal for automated placement

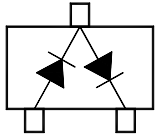
### Pin Configuration



1. Anode1 2. Cathode2  
3. Cathode1、Anode2

### Equivalent Circuit

3. Cathode1、Anode2



1. Anode1 2. Cathode2

Marking Code : A7

### Electrical Characteristics (TA = 25°C)

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	85	V
Reverse Voltage	$V_R$	75	V
Average Rectified Forward Current (Double Diode Load)	$I_{F(AV)}$	200	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	0.5	A
at $t = 1$ s		1	
at $t = 1$ ms		4.5	
Maximum Power Dissipation	$P_D$	350	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{STG}$	-65 to +150	°C

### Electrical Characteristics (TA = 25°C)

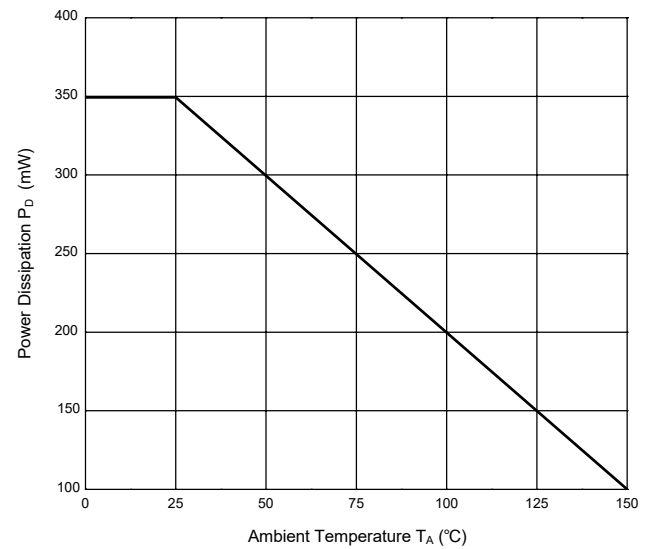
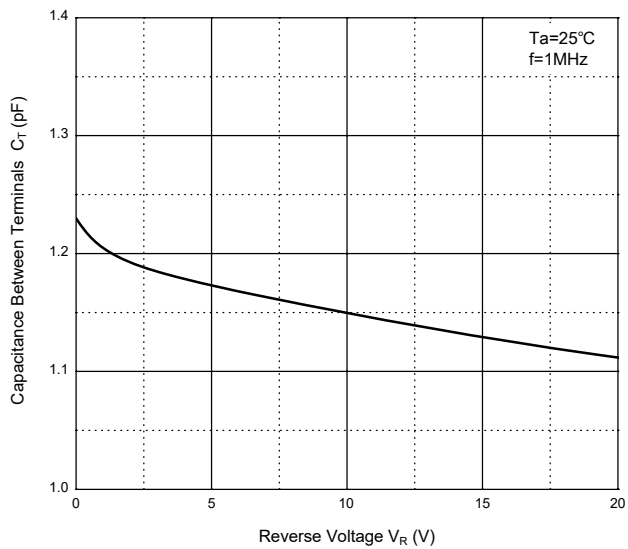
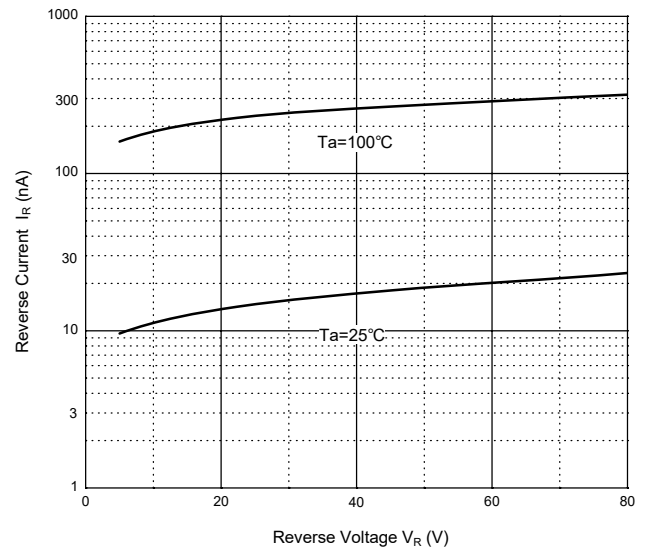
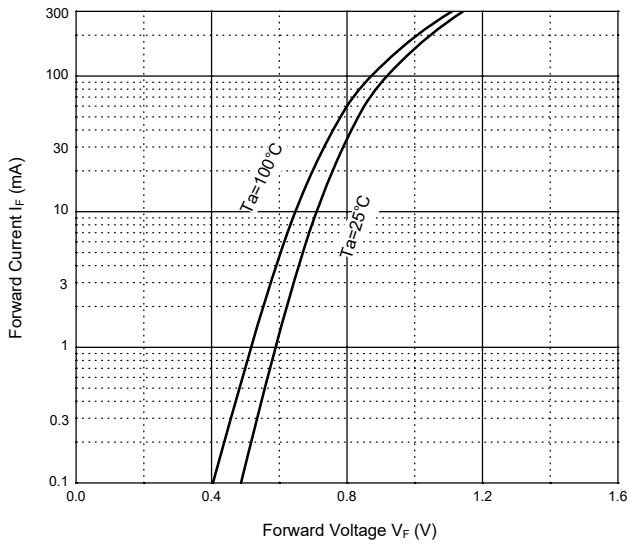
Parameter	Symbol	Max.	Unit
Forward Voltage	$V_F$	0.715	V
at $I_F = 1$ mA		0.855	
at $I_F = 10$ mA		1	
at $I_F = 50$ mA		1.25	
Reverse Current	$I_R$	0.03	$\mu$ A
at $V_R = 25$ V		1	
at $V_R = 75$ V		30	
at $V_R = 25$ V, $T_J = 150$ °C		50	
Typical Junction Capacitance	$C_j$	1.5	pF
at $V_R = 4$ V, $f = 1$ MHz			
Maximum Reverse Recovery Time	$T_{rr}$	4	nS



# BAV99<sup>\*</sup>

## Silicon Epitaxial Planar Switching Diode

### Typical Characteristic Curves





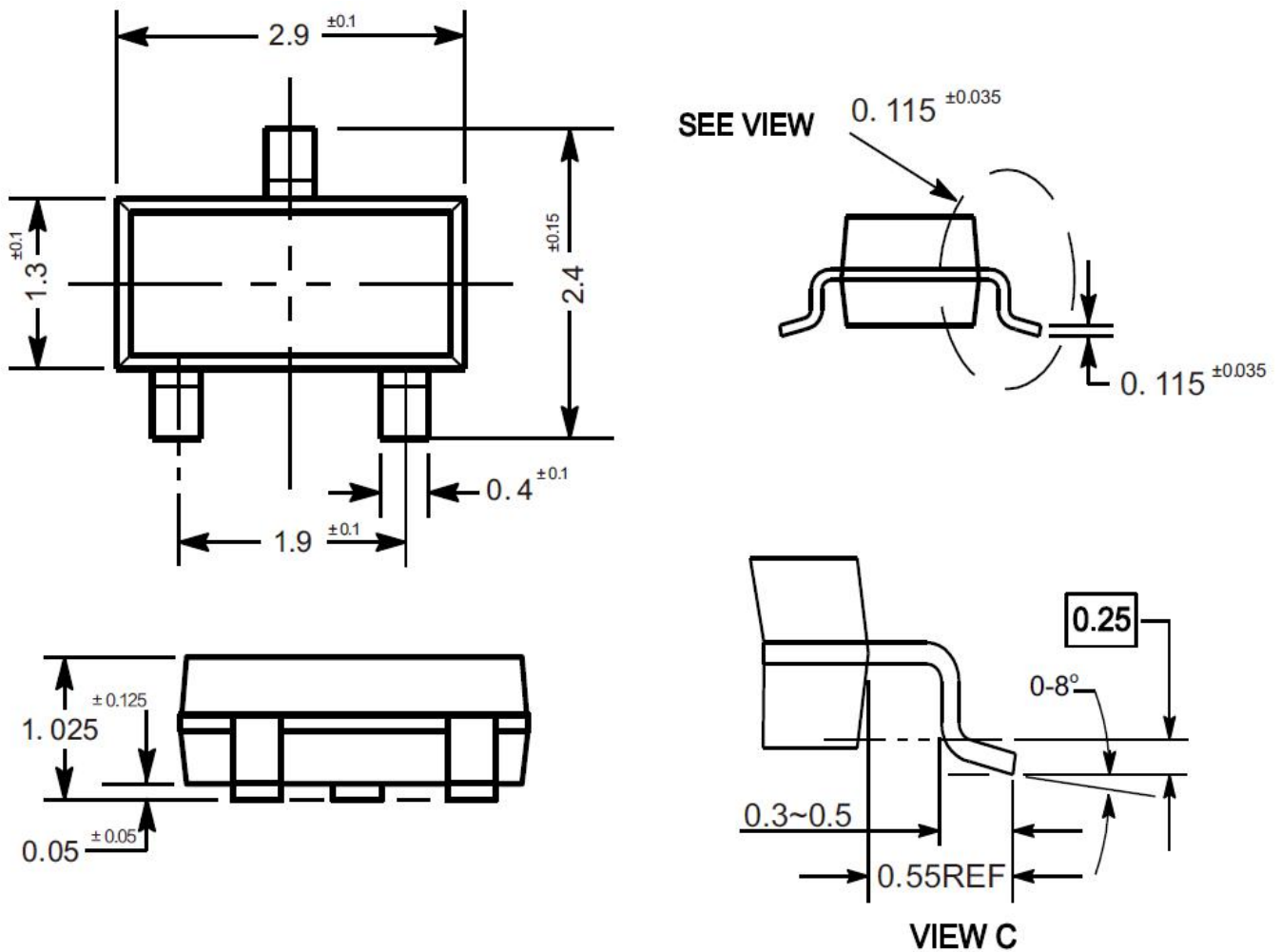
# BAV99<sup>†</sup>

## Silicon Epitaxial Planar Switching Diode

### Package Outline

SOT-23

Dimensions in mm



### Ordering Information

Device	Package	Shipping
BAV99	SOT-23	3,000PCS/Reel&7inches